Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	16	((etch adj stop) etch-stop) with "'10.sup.19'"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:27
L2	42	((etch adj stop) etch-stop) with "'10.sup.18'"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:28
L3	0	("'Si.sub.1-x'" adj "'Ge.sub.x'" and (relaxed same (dop\$3 concentration)) and graded).clm.	US-PGPUB	OR	ON	2007/01/03 13:32
L4	125	438/936.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:37
L5	948	438/258.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 14:33
L6	138	438/590.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 14:33
S1	2	"6689211".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/03 13:27
S2	2	"6521041".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	OFF	2004/05/11 13:49

CO	470	//II200100022C4II\	LIC DODI ID	OB	OFF	2004/12/17 12:20
S3	176	(("20010003364") or	US-PGPUB;	OR	OFF	2004/12/17 12:30
		("20010007789") or	USPAT			
		("20020043660") or				
		("20020084000") or				
		("20020096717") or				
		("20020100942") or				
		("20020123167") or				
		("20020123183") or				
		("20020125471") or				
		("20020168864") or				
1		("20030003679") or				
		("20030013305") or		•		
		("20030034529") or				
	•	("20030057439") or				
		("20030102498") or				
		("20030119280") or				
		("20030127646") or				
		("20030139000") or		1		
		("20030157787") or		1		
		("20030160300") or				
		("20030178681") or				
		("20030189229") or				
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		("20030203600") or		1		
		("20030207127") or				
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		("20030227057") or				
		("20030230778") or				
		("20030232467") or				
		("20040005740") or				
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		("20040012075") or				
		("20040014304") or			1	
		("20040018699") or				×
1		("20040031979") or				
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		("20040041174") or			-	
		("20040041210") or				
		("20040048091") or			1	
		("20040048454") or				
		("20040051140") or				
		("20040053477") or				
		("20040075149") or ("4704302") or				1 111
		("4710788") or ("4987462") or				
		("4990979") or ("4997776") or				
		("5155571") or ("5177583") or				
1		("5240876") or ("5241197") or				1.10
		("5250445") or ("5291439") or				
		("5298452") or ("5316958") or				
		( 5298452 ) 01 ( 5316958 ) 01 ( "5399522") or ("5424243") or				
1/3/07	2:36:00 PM					Page 2
C:\Docu	ments and Se	("5426069") or ("5426316") or   ("5439843") or ("5461250") or   ("5439843") or ("5461250") or	paces\1060385	2.wsp		
1		("5479033") or ("5573743") or				
						·

S4	0	("'Si.sub.'\$" adj "'Ge.sub.'\$") same (etch etch-stop) same relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/17 12:31
S5	7	(("'Si.sub.1-x'" adj "'Ge.sub.x'")("Si. sub.1-y'" adj "'Ge.sub.y'")("'Si.sub. 1-z'" adj "'Ge.sub.z'")) same (etch etch-stop) same relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/17 12:34
S6	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("'Si.sub. 1-?'" adj "'Ge.sub.?'"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:20
S7	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("'Si.sub. 1-?'" adj "'Ge.sub.?'") not (silicon adj Nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:40
S8	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?'" adj "'Ge.sub.?'") not (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:45
S9	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?'" adj "'Ge.sub.?'") not near2 (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:46
S10	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?'" adj "'Ge.sub.?'") not (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:52
S11	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?" adj "Ge.sub.?") not nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF .	2005/04/12 10:53
S12	3315	(etch-stop (etch adj stop) (etch adj barrier)) near3 (silicon Si ("'Si.sub. 1-?'" adj "'Ge.sub.?'") not nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:52
S13	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?" adj "Ge.sub.?"") not near3 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:53

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S14	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?" adj "'Ge.sub.?"") not near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 11:02
S15	169	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?" adj "'Ge.sub.?"")) with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 14:42
S16	3	(etch-stop (etch adj stop) (etch adj barrier)) near2 (("Si.sub.1-x" adj "Ge.sub.x")) with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 14:44
S17	2	(etch-stop (etch adj stop) (etch adj barrier)) near2 (("Si.sub.1-y" adj "Ge.sub.y"")) with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 14:45
S18	1	(etch-stop (etch adj stop) (etch adj barrier)) near2 (("Si.sub.1-z" adj "Ge.sub.z")) with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 14:45
S19	291	(etch adj stop) near2 (silicon adj dioxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:22
S20	4	(etch adj stop) near2 (silicon adj dioxide) with relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:27
S21	0	(etch adj stop) near2 "SiO.sub.2" with relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:27
S22		(etch adj stop) near2 SiO with relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:27
S23	0	(etch adj stop) near2 (Silicon adj oxide) with relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:28

S24	33	("'Si.sub.1-x'" adj "'Ge.sub.x'") with relaxed with graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 10:30
S25	12	(("2002140031") or ("2003003679") or ("5013681") or ("5548128") or ("5607876") or ("5906951") or ("6154475") or ("6372593") or ("6489639") or ("6521041") or ("6591321") or ("6597016") or ("6674150") or ("6689211")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/05 16:30
S26	236	("Si.sub.1-x" adj "Ge.sub.x") and (SiN (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:33
S27	11	(("Si.sub.1-x" adj "Ge.sub.x") same relaxed same graded) and (SiN (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:47
S28	2	(("Si.sub.1-x" adj "Ge.sub.x") same relaxed same graded) and (TiN (titanium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:48
S29	0	(("Si.sub.0.5" adj "Ge.sub.0.5") same relaxed same graded) and (SiN (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:49
S30	28	(("Si.sub.1-x" adj "Ge.sub.x") same relaxed same graded) and (etch-stop (etch adj stop) mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF ,	2005/10/06 08:59
S31	0	(("Si.sub.1-x" adj "Ge.sub.x") same relaxed same graded) and (etch adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:59
S32	5	(("5089872") or ("5242847") or ("5548128") or ("5607876") or ("5821577")).PN.	US-PGPUB; USPAT	OR .	OFF	2006/02/22 11:41
S33	412	(SiGe ("'Si.sub.1-x'" adj "'Ge.sub. x'")) same relaxed same graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/14 15:28

S34	403	(SiGe ("'Si.sub.x-1" adj "'Ge.sub. x'")) same relaxed same graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/14 15:29
S35	412	(SiGe ("'Si.sub.1-x'" adj "'Ge.sub. x'")) same relaxed same graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/14 15:36
S36	63	(SiGe ("'Si.sub.1-x'" adj "'Ge.sub. x'")) same relaxed same graded same (dope doped doping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/14 15:36
S37	719	257/18,19,190-194.ccls. and @pd>"20040520"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:33
S38	0	"'Si.sub.'"\$ adj "'Ge.sub.'"\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/31 17:02
S39	643	"'Si.sub.1-x'" adj "'Ge.sub.x'"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/31 17:12
S40	184	"'Si.sub.1-x'" adj "'Ge.sub.x'" and relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/31 17:12
S41	121	"'Si.sub.1-x'" adj "'Ge.sub.x'" and relaxed and graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/31 17:26
S42	80	"'Si.sub.1-x'" adj "'Ge.sub.x'" and (relaxed same (dop\$3 concentration)) and graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:31
S43	50	"'Si.sub.1-y'" adj "'Ge.sub.y'" and (relaxed same (dop\$3 concentration)) and graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/31 17:45

